

HBS602 THRU HBS610

SINGLE PHASE GLASS PASSIVATED BRIDGE RECTIFIERS

Features

- ♦ Surface mount bridge, small package;
- ♦ Ideal for printed circuit boards;
- Glass passivated chip junction;
- ◆ High forward current capability up to 6.0A;
- ♦ High surge current capability;
- High heat dissipation capability;
- ◆ Low profile package;
- Low forward voltage drop;
- Plastic package has Underwrites Laboratory Flammability Classification 94V-0;

Mechanical Data

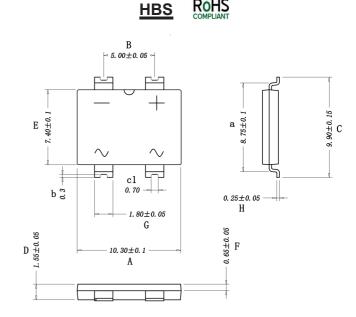
Case: JEDEC HBS Molded plastic body

Mounting Position: Any

High temperature soldering guaranteed: Solder Reflow

260 ℃,10seconds

Polarity: As marked on body



Dimensions in inches and (millimeters)

Maximum Ratings And Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwisespecified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Parameter	SYMBOLS	MDD HBS602	MDD HBS604	MDD HBS606	MDD HBS608	MDD HBS610	UNITS
Marking Code							
Maximum repetitive peak reverse voltage	Vrrm	200	400	600	800	1000	V
Maximum RMS voltage	VRMS	140	280	420	560	700	V
Maximum DC blocking voltage	VDC	200	400	600	800	1000	V
Maximum average forward rectified current at T _A =25°C	I _{F(AV)}			6.0			A
Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	170					А
Maximum instantaneous forward voltage drop per diode at 6A	V _F	1.10					V
Maximum DC reverse current Ta=25°C at rated DC blocking voltage Ta=125°C	I _R	5 100					μA
Typical capacitance (note1)	C¹	43					pF
Typical thermal resistance	R _{eJA}	68					
	R _{eJC}	10					°C/W
	R _{eJL}	22					
Operating junction and Storage Temperature Range	T_{j} , T_{STG}	-55 to +150					°C

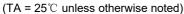
Note1: Measured at 1.0MHz and applied reverse voltage of 5.0V DC;

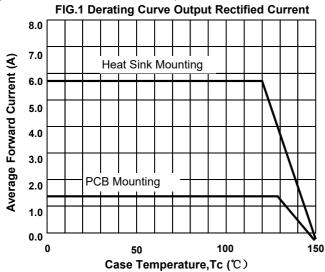
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Ratings And Characteristic Curves





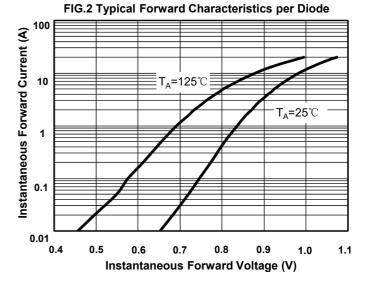


FIG.3 Maximum Non-Repetitive Peak Forward Surge

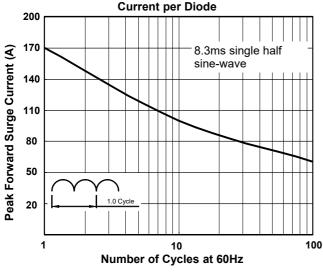


FIG.4 Typical Reverse Characteristics per Diode

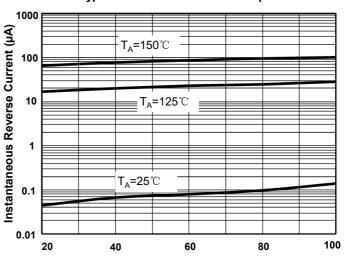
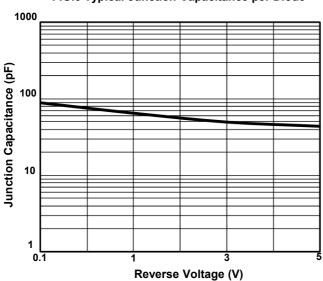


FIG.5 Typical Junction Capacitance per Diode



Percent of Rated Peak Reverse Voltage (%)

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